#### **FORM PTO-1449**

### LIST OF PATENTS AND OTHER ITEMS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

O PE (Use several sheets if necessary)

ATTY.	DOCKET
255/23	6 P00-002T

**SERIAL NO.** 09/621/028

**APPLICANT:** 

Bergman, Eric J. et al.

FILING DATE: July 21, 2000 GROUP:

		HIS PATENT DOCUMENTS						
		U.S. PATENT DOCUMENTS						
EXAM INIT	INER IAL	CNTB	BARTON MENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
Z	E	AA	5,055,138	10/8/91	Slinn			
		AB	5,120,370	6/9/92	Mori et al.			
		AC	5,647,386	7/15/97	Kaiser			
		AD	5,181,985	1/26/93	Lampert et al.			
		AE	5,503,708	4/2/96	Koizumi et al.			
		AF	5,464,480	11/7/95	Matthews			
		AH	5,308,745	5/3/94	Schwartzkopf			
		ΑI	4,695,327	9/22/87	Grebinski			
		AJ	5,632,847	5/27/97	Ohno et al.			
		AK	5,911,837	6/15/99	Matthews			
		AL	5,705,089	1/6/98	Sugihara et al.		77	
		AM	5,244,000	9/14/93	Stanford et al.		ONTIC	
		AN	5,714,203	2/3/98	Schellenberger et al.		TECHNOLOGY	REC
		AO	5,896,875	4/27/99	Yoneda			<u>- — — — — — — — — — — — — — — — — — — —</u>
		AP	4,974,530	12/4/90	Lyon	-	CENTER OF	VED
		AQ	5,055,138	10/8/91	Slinn		1700	
		AR	5,120,370	6/9/92	Mori et al.			
		AS	5,647,386	7/15/97	Kaiser			
		AT	5,248,380	9/28/93	Tanaka	-	,	
		AU	5,520,744	5/28/96	Fujikawa et al.			
	\	AV	5,415,191	5/16/95	Mashimo et al.			
,Z		AW	5,658,615	8/19/97	Hasebe et al.			

EXAMINER:	EL-Arini	DATE CONSIDERED:	3/6/02	

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Information Disclosure Statement - Section 9 PTO-1449

#### **FORM PTO-1449** ATTY. DOCKET SERIAL NO. 255/236 P00-0021 09/621/028 LIST OF PATENTS AND OTHER ITEMS FOR APPLICANT'S APPLICANT: INFORMATION DISCLOSURE STATEMENT Bergman, Eric J. et al. NOV 0 1 2000 **FILING DATE: GROUP:** (Use several sheets if necessary) July 21, 2000 TRADENAN 25 AX 1/12/99 Chao et al. 5,858,107 AY 5,235,995 8/17/93 Bergman et al. 1/3/95 Kashiwase et al. ΑZ 5,378,317 BA 5,971,368 10/26/99 Nelson et al. ZE 8/10/93 BB 5,234,540 Grant et al. FOREIGN PATENT DOCUMENTS TRANSLATION **EXAMINER** SUB YES NO INITIAL DOCUMENT NUMBER DATE COUNTRY **CLASS CLASS** BC 0 548 596 A2 6/3/93 Europe BD 0 344 764 12/6/89 Europe BE 0 702 399 3/20/96 Europe BF GB 2 287 827 9/27/95 United Kingdom m

12	C	BG	JP52-12063	Japan		NO		
	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
2	F	вн	Abstract of JP 3041729 p	ublished 2/22/91		IVE 200		
		BI	Abstract of JP 1008630, p	oublished 1/12/89		D		
		ВЈ	Abstract of Japanese App	oln. No. 63-16127 published July 31, 1989.	•	00		
	BK Abstract of Japanese Appln. No. 52-100473 published March 14, 1979.							
BL Abstract of Japanese Appln. No. 1-192712 published March 12, 1992.								
		ВМ		apanese Appln. No. 1984-125760 publishe				
		BN	Proceedings on Materials	Wet Cleaning Strategies for Obtaining His Research Society, Spring Meeting, San Fi	rancisco, CA April 12	2-13, 1993, p. 35 (1993)		
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26	Ē.	BP	Nelson, Steve, "Ozonated	i water for photoresist removal" Solid State	e Technology, pp. 107	7-112 (July 1999)		

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# FORM PTO-1449 LIST OF PATENTS AND OTHER ITEMS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT NOV © 1 2000 (Use several sheets if necessary) ATTY. DOCKET 255/236 P00-0021 APPLICANT: Bergman, Eric J. et al. FILING DATE: July 21, 2000 GROUP:

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SERIAL NO. 09/621/028

APPLICANT:

Bergman, Eric J. et al.

FILING DATE: July 21, 2000 **GROUP:** 

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